









B2D20065TF

650V ▲ 2x10A ▲ SiC SCHOTTKY DIODE

SILICON CARBIDE SiC SCHOTTKY DIODE ▲ THT type

Common cathode circuit configuration

Easy paralleling due to positive V_F temperature coefficient

Temperature independent switching

Ultra-low forward voltage and high surge current

TO3PF-3L package ▲ Electrical insulated mounting tab

Item (T _C = 25°C, unless otherwise noted)		Characteristics
Operating Temperature Range	Tı	-55°C to +175°C
Storage Temperature Range	Ts	-55°C to +175°C
Repetitive Peak Reverse Voltage	V_{RRM}	650V
Continuous Forward Current at T _C = 140°C Note 1	I _F	10A
Continuous Forward Current at T _C = 140°C Note 2	I _F	20A
Total Capacitive Charge (T _J = 25°C) Note 2	Qc	60nC
Diode Forward Voltage (T _J = 175°C, I _F = 10A) Note 1	V_{F}	1.62V
Power Dissipation Note 1	P _{TOT}	77W

Notes

Per leg
 Per device

APPLICATIONS

EV Charging	Industrial Inverters	Motors & Drives	Power Factor Correction	Renewable Energy	SMPS	UPS
₹ /•			PFC	*		

PIN DESCRIPTION

Circuit Diagram	Outline • Front View	Pin No.	Description
	1 2 3	1 2 3	Anode Diode 1 Common Cathode Anode Diode 2



ABSOLUT MAXIMUM RATINGS ▲ T_C = 25°C, unless otherwise noted

ltem	Condition	Symbol		Unit
Repetitive Peak Reverse Voltage		V_{RRM}	650	V
Non-Repetitive Peak Reverse Voltage		V_{RSM}	650	V
Continuous Forward Current	T _C = 25°C	I _F	25 Note 1 / 50 Note 2	Α
Continuous Forward Current	T _C = 140°C	I _F	10 Note 1 / 20 Note 2	Α
Non-Repetitive Forward Surge Current	$T_C = 25$ °C, $t_p = 10$ ms, Half Sine Wave	I _{FSM}	70 Note 1	Α
I ² t Value	$T_C = 25^{\circ}C$, $t_p = 10$ ms	∫i²dt	24 Note 1	A^2s
Power Dissipation	T _C = 25°C	P_{TOT}	77 Note 1	W
Power Dissipation	T _C = 110°C	P_{TOT}	33 Note 1	W
Operating Junction Temperature		TJ	-55 to +175	°C
Storage Temperature Range		T_{STG}	-55 to +175	°C
TO-3PF Mounting Torque	M3 Screw		0.6	Nm

Notes

1: Per leg

2: Per device

ELECTRICAL CHARACTERISTICS A PER LEG

Item	Condition	Symbol	Min.	Тур.	Max.	Unit
Static Characteristics		•				
DC Blocking Voltage	T _J = 25°C	650			V	
Diode Forward Voltage	$I_F = 10A, T_J = 25^{\circ}C$	V_{F}		1.30	1.50	V
Diode Forward Voltage	$I_F = 10A, T_J = 175^{\circ}C$	V_{F}		1.62	2.06	V
Reverse Current	$V_R = 650V$, $T_J = 25$ °C	I _R		1	70	μΑ
Reverse Current	$V_R = 650V$, $T_J = 175$ °C	I _R		20	200	μΑ
Item	Condition	Symbol	Min.	Тур.	Max.	Unit
Dynamic Characteristics	Continuen	o y misor		.) [5.	TVIGA	J
	$V_R = 400V$, $T_J = 25$ °C					
Total Capacitive Charge	$Q_C = \int_0^{V_R} C(V) dV$	Qc		30		nC
Total Capacitance	$V_R = 1V$, $f = 1MHz$, $T_J = 25$ °C	С		470		pF
Total Capacitance	$V_R = 300V, f = 1MHz, T_J = 25^{\circ}C$	С		54		pF
Total Capacitance	$V_R = 600V$, $f = 1MHz$, $T_J = 25$ °C	С		53		pF
Capacitance Stored Energy	$V_R = 400V$, $T_J = 25$ °C	Ec		7		μЈ

THERMAL RESISTANCE PERFORMANCE

ltem	Symbol	Min.	Тур.	Max.	Unit
Thermal Resistance, Junction to Case, per Leg	R _{θ,JC}		1.929		K/W
Thermal Resistance, Junction to Case, per Device	$R_{\theta,JC}$		0.965		K/W



REFERENCE DATA A TYPICAL PERFORMANCE PER LEG

Fig. 1 • Typical Forward Characteristics I_F vs. V_F

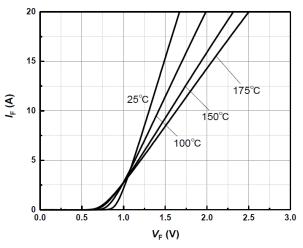


Fig. 2 • Typical Reverse Current I_R as function of Reverse Voltage V_R

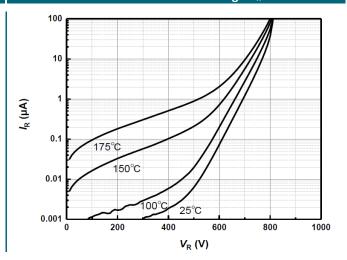


Fig. 3 • Diode Forward Current I_F as function of Case Temperature T_C (D = Duty Cycle)

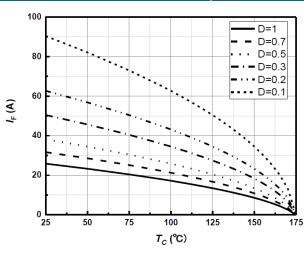


Fig. 4 • Typical Capacitance C as function of Reverse Voltage V_R, C = f(V_R), T_J = 25°C, f = 1MHz

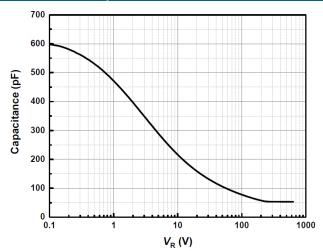


Fig. 5 • Typical Reverse Charge Q_C as function of Reverse Voltage V_R

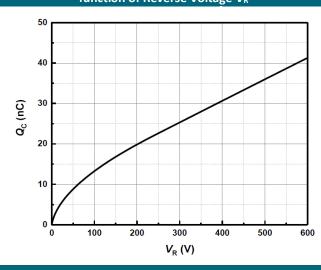
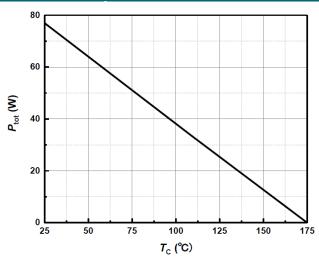


Fig. 6 • Power Dissipation P_{TOT} as function of Case Temperature T_C



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REFERENCE DATA A TYPICAL PERFORMANCE PER LEG

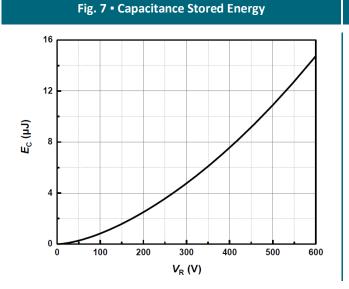
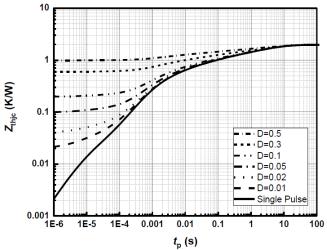
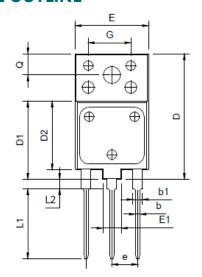


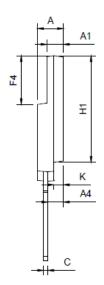
Fig. 8 • Maximum Transient Thermal Impedance, Z_{thjc} = f(t), Parameter: D = t/T

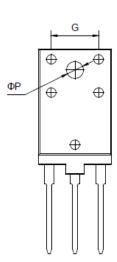




PACKAGE OUTLINE









Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)
Α	5.30	5.50	5.70
A1	2.80	3.00	3.20
b	0.66	0.86	0.95
b1	1.80	2.00	2.20
A4	3.10	3.30	3.50
С	0.80	0.90	1.00
D	26.30	26.50	26.70
D1	16.30	16.50	16.70
D2	14.40	14.50	14.70
Р	3.40	3.60	3.80
Е	15.30	15.50	15.70

Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)
E1	3.80	4.00	4.20
e	5.15	5.45	5.75
G	9.70	9.90	10.10
Q	4.35	4.50	4.65
L1	14.60	14.80	15.00
L2	2.30	2.50	2.70
K	1.80	2.00	2.20
F4	9.80	10.00	10.20
H1	22.80	23.00	23.20
K	1.80	2.00	2.20

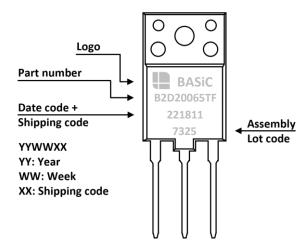
TO3PF-3L package ▲ Epoxy meets UL94-V0

ORDERING INFORMATION

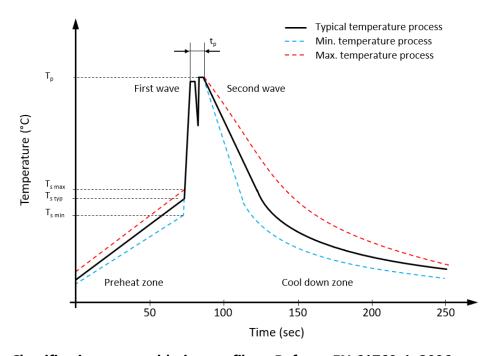
Part Number	Package	Packing	Tube Qty.	Inner Box Qty.	Outer Box Qty.
B2D20065TF	TO3PF-3L	Tube	30pcs	300pcs	3,000pcs



PART MARKING



RECOMMENDED WAVE SOLDERING PROFILE & THT PACKAGE



Classification wave soldering profile ▲ Refer to EN 61760-1: 2006

Profile Features		Value ▲ Sn-Pb Assembly	Value ▲ Pb-free Assembly
Preheat temperature min.	T _{s min}	100 °C	100 °C
Preheat temperature typical	T _{s typ}	120 °C	120 °C
Preheat temperature max.	T_{smax}	130 °C	130 °C
Preheat time t_s from T_{smin} to T_{smax}	ts	70 seconds	70 seconds
Peak temperature	T_p	235 °C to 260 °C	245 °C to 260 °C
Time of actual peak temperature	tp	Max. 10 seconds Max. 5 second each wave	Max. 10 seconds Max. 5 second each wave
Ramp-down date min.		~ 2 °C/second	~ 2 °C/second
Ramp-down rate typical		~ 3.5 °C/second	~ 3.5 °C/second
Ramp-down rate max.		~ 5 °C/second	~ 5 °C/second
Time 25°C to 25°C		4 minutes	4 minutes

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REVISION TABLE

Revision	Date	Status	Notes
001	30/09/2022	Initial release	Initial publication

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